

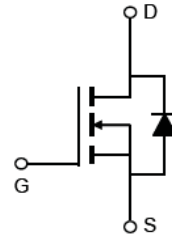
N-Channel Power MOSFET

Features

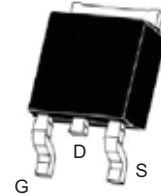
- 600V, 7A, $R_{DS(ON)}(Max.) = 1.3\Omega @ V_{GS} = 10V$.
- Low Crss
- Fast Switching
- 100% Avalanche Tested

Application

- Adapter
- LCD Panel Power
- E-Bike Charger
- Switching Mode Power Supply
- Halogen-free



Schematic diagram



TO-252 -2L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
7N600	RMP7N600LD	TO-252-2L	--	--	--

Absolute Maximum Ratings $T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage ^a	600	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current-Continuous, $T_c = 25^\circ\text{C}$	7	A
	Drain Current-Continuous, $T_c = 100^\circ\text{C}$	4	A
I_{DM}	Drain Current-Pulsed ^b	28	A
P_D	Maximum Power Dissipation @ $T_J = 25^\circ\text{C}$	106	W
EAS	Single Pulsed Avalanche Energy ^d	245	mJ
T_J, T_{STG}	Operating and Store Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-Case Max.	1.18	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient Max	110	$^\circ\text{C/W}$

Electrical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted

Off Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	600	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	-	-	1	μA
I_{GSS}	Forward Gate Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 30V$	-	-	± 100	nA

On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance ^c	$V_{GS} = 10V, I_D = 3.5A$	-	1.0	1.3	Ω

Dynamic Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
C_{iss}	Input Capacitance	$V_{DS} = 25V,$ $V_{GS} = 0V,$ $f = 1.0MHz$	-	1135	-	pF
C_{oss}	Output Capacitance		-	88	-	pF
C_{rss}	Reverse Transfer Capacitance		-	4.6	-	pF

On Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300V, I_D = 7A,$ $R_G = 10\Omega, V_{GS} = 10V$	-	19	-	ns
t_r	Turn-On Rise Time		-	21	-	ns
$t_{d(off)}$	Turn-Off Delay Time		-	42	-	ns
t_f	Turn-Off Fall Time		-	19	-	ns
Q_g	Total Gate Charge	$V_{DS} = 480V, I_D = 7A,$ $V_{GS} = 10V$	-	24	-	nC
Q_{gs}	Gate-Source Charge		-	4.9	-	nC
Q_{gd}	Gate-Drain Charge		-	9.5	-	nC

Drain-Source Diode Characteristics

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
I_S	Drain-Source Diode Forward Continuous Current	$V_{GS} = 0V$	-	-	7	A
I_{SM}	Maximum Pulsed Current	$V_{GS} = 0V$	-	-	28	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0V, I_S = 7A$	-	-	1.4	V

Notes:

a. $T_J = -55^\circ\text{C}$ to $+150^\circ\text{C}$

b. Repetitive rating; pulse width limited by maximum junction temperature.

c. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$

d. $L = 10mH, V_{DD} = 50V, I_{as} = 7A, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$

RATING AND CHARACTERISTICS CURVES (RMP7N600LD)

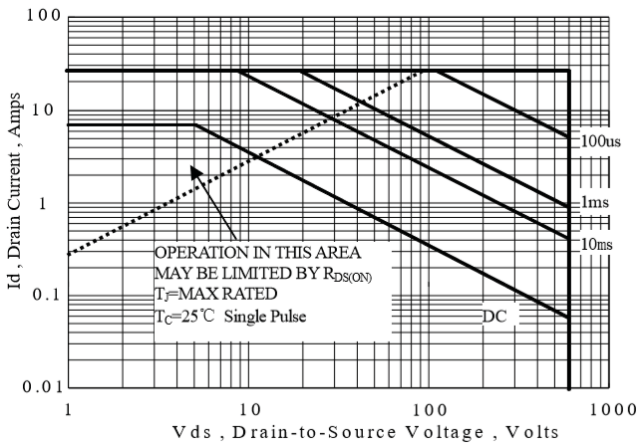


Figure 1. Maximum Safe Operating Area

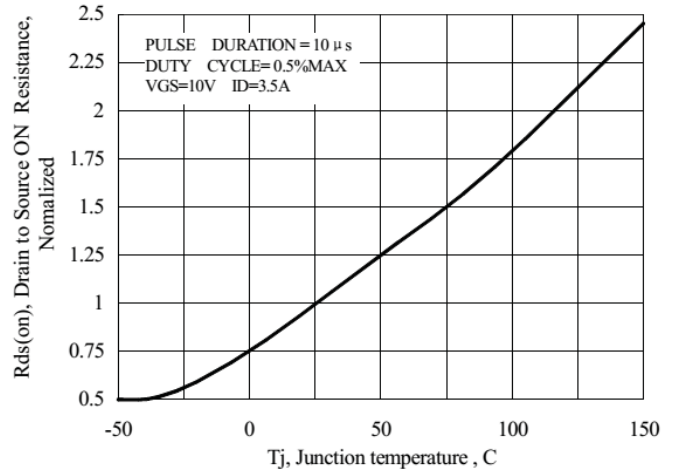


Figure 2. Normalized On-Resistance Variation with Temperature

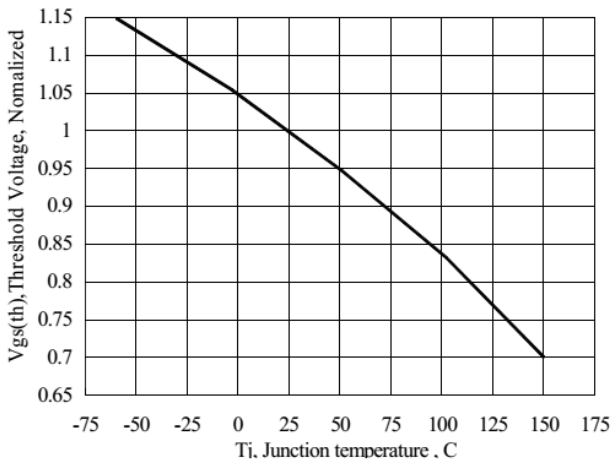


Figure 3. Typical Theshold Voltage vs Junction Temperature

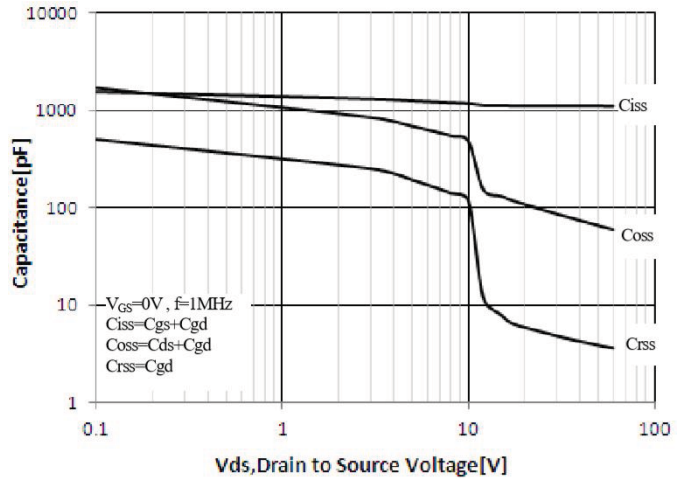


Figure 4. Capacitance Characteristics

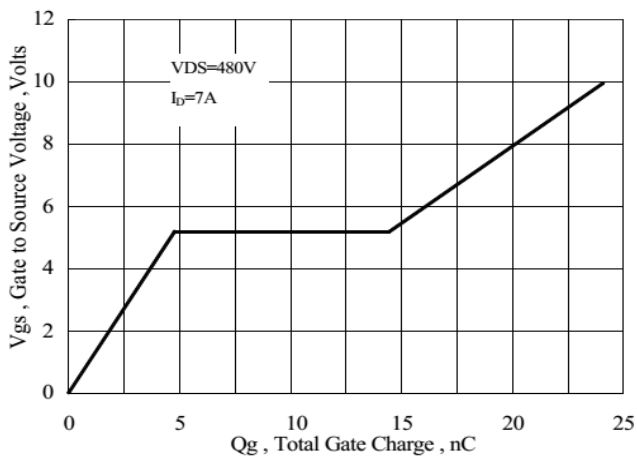


Figure 5. Gate Charge Characteristics

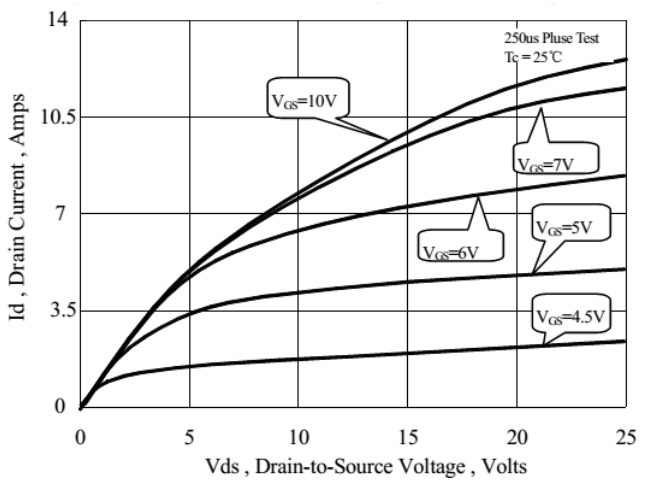


Figure 6. On-State Characteristics

RATING AND CHARACTERISTICS CURVES (RMP7N600LD)

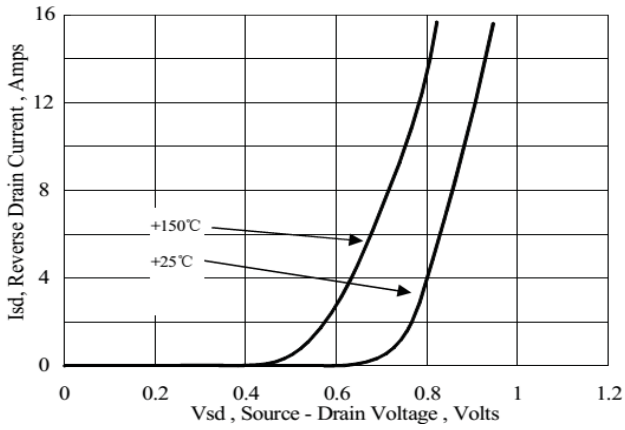


Figure 7. Typical Body Diode Transfer Characteristics

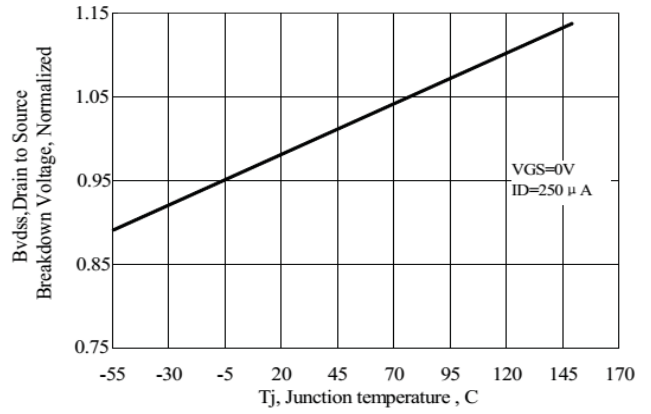


Figure 8. Typical Breakdown Voltage vs Junction Temperature

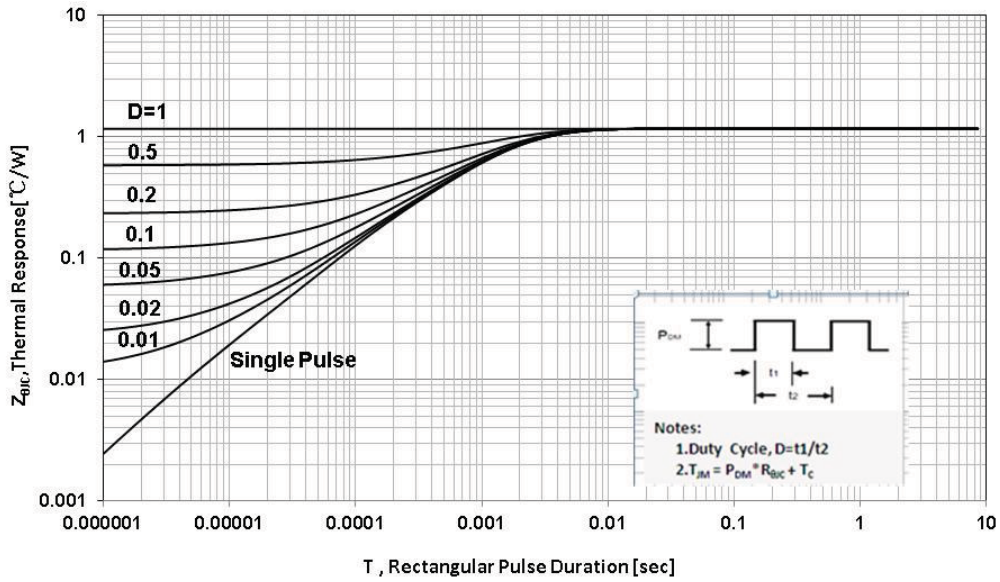
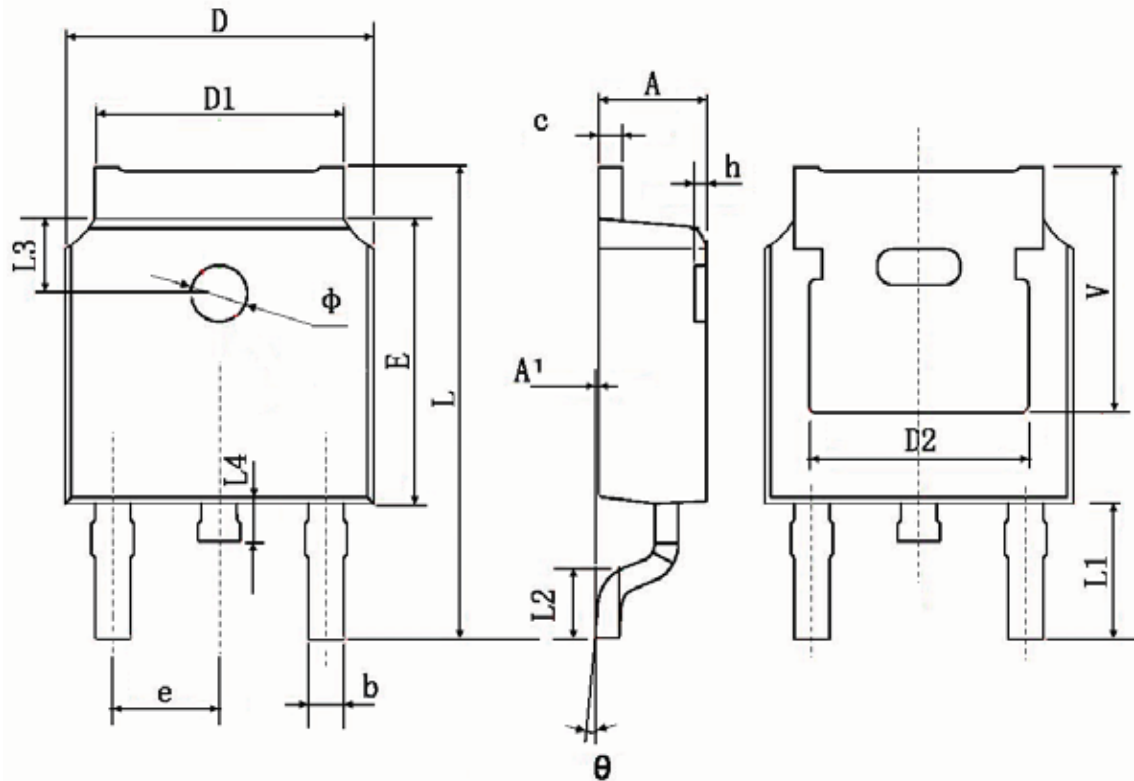


Figure 9. Normalized Effective Transient Thermal Impedance With Pulse Duration

TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.83 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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